

DRYING PROCESS FOR LOW-K DIELECTRIC FILMS

Abstract of Disclosure

A method for drying and removing contaminants from a low-k dielectric film of an integrated circuit wafer, the method comprising exposing the low k dielectric layer to photons; and simultaneously with, prior to, or subsequent to the photon exposure, exposing the substrate to a process effective to remove the contaminants without causing degradation of the low k dielectric layer, wherein the process is selected from the group consisting of a heat process, a vacuum process, an oxygen free plasma process, and combinations thereof.

Figures